



40V 150°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C	
40V	7.5mΩ @ V _{GS} = 10V	49.1A	

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor controls
- Power-management functions
- DC-DC converters

Features and Benefits

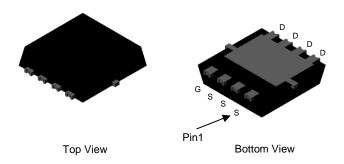
- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- Low RDS(ON) Ensures On-State Losses are Minimized
- 100% Unclamped Inductive Switching, Test in Production Ensures More Reliable and Robust End Application
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMT47M2SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

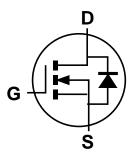
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.025 grams (Approximate)

PowerDI3333-8/SWP (Type UX)





Equivalent Circuit

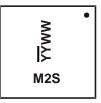
Ordering Information (Note 4)

Part Number	Package	Packing		
Part Number	Fackage	Qty.	Carrier	
DMT47M2SFVWQ-7	PowerDI3333-8/SWP (Type UX)	2,000	Tape & Reel	
DMT47M2SFVWQ-13	PowerDI3333-8/SWP (Type UX)	3,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Note 6), V _{GS} = 10V	T _C = +25°C T _C = +70°C	I _D	49.1 39.2	А
Continuous Drain Current (Note 5), $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		lo	15.4 12.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	196	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	30.8	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle	lsм	196	Α	
Avalanche Current, L = 0.1mH	las	24.7	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	30.5	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		PD	2.67	W
Thermal Resistance, Junction to Ambient (Note 5)	RθJA	46.5	°C/W	
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	27.1	W
Thermal Resistance, Junction to Case (Note 6)		R _θ JC	4.61	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

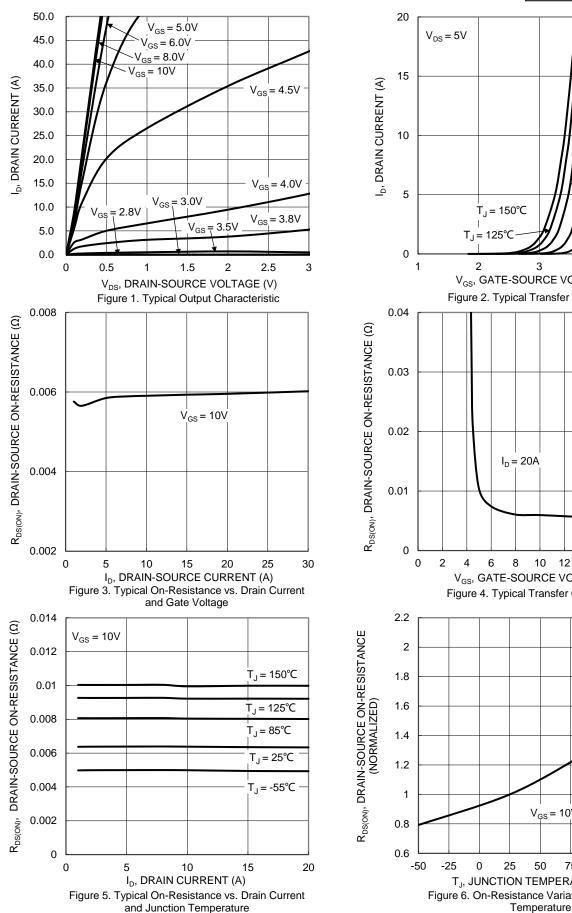
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40	_		V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V _{DS} = 32V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	2	2.5	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	5.9	7.5	mΩ	V _G S = 10V, I _D = 20A	
Diode Forward Voltage	V _{SD}	_	0.88	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	897	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	530		pF		
Reverse Transfer Capacitance	Crss	_	12.4				
Gate Resistance	Rg	_	2.07	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg		12.1	_		V _{DS} = 20V, I _D = 20A, V _{GS} = 10V	
Gate-Source Charge	Q _{gs}	_	2.0	_	nC		
Gate-Drain Charge	Q_{gd}	_	1.9	_			
Turn-On Delay Time	tD(ON)	_	5.36	_		$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 20A$	
Turn-On Rise Time	t _R	_	4.54	_			
Turn-Off Delay Time	tD(OFF)		12.1	_	ns		
Turn-Off Fall Time	tϝ	_	5.59	_			
Body Diode Reverse Recovery Time	t _{RR}		39.1	_	ns	1 00A 15/11 400A/c	
Body Diode Reverse Recovery Charge	QRR	_	53.3	_	nC	I _F = 20A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.







 $T_J = 85^{\circ}C$ T_J = 150°C T_J = 25°C T_J = -55°C 3 4 5 V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic $I_{D} = 20A$ 10 12 14 16 18 8 20 V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 4. Typical Transfer Characteristic $V_{GS} = 10V, I_D = 20A$ 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with Junction





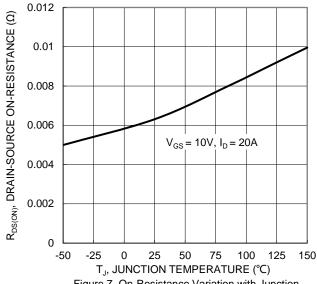


Figure 7. On-Resistance Variation with Junction Temperature

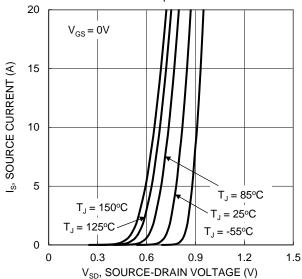
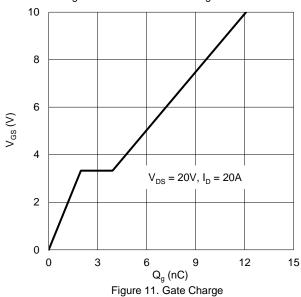


Figure 9. Diode Forward Voltage vs. Current



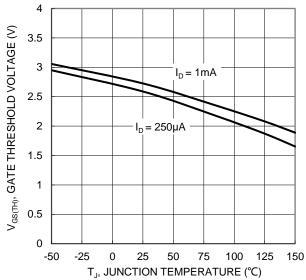
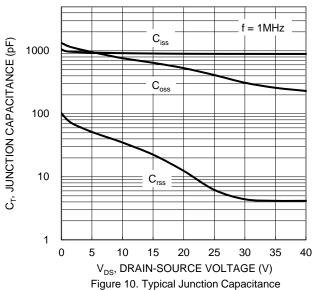


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ Limited 100 ID, DRAIN CURRENT (A) 10 $P_W = 10 \mu s$ $P_W = 100 \mu \hat{s}$ $P_W = 10 ms$ T_{J(Max)} = 150°C $P_W = 100 ms$ $T_C = 25^{\circ}C$ Single Pulse $P_W = 1s$ DUT on Infinite Heatsink $V_{GS} = 10V$ 0.01 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



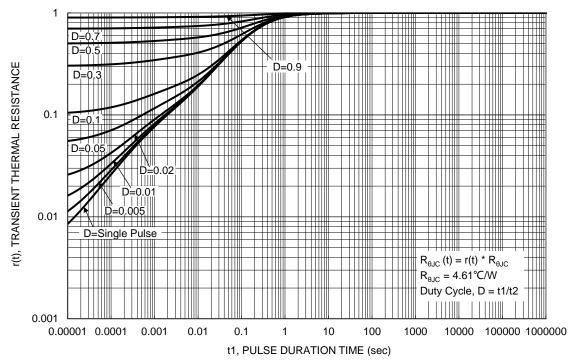


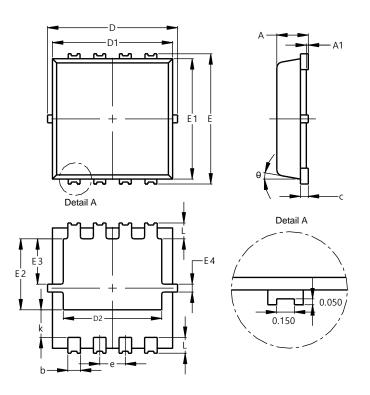
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

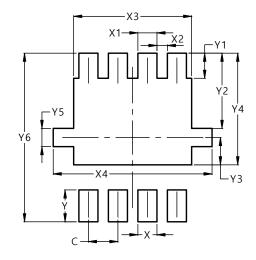


PowerDI3333-8/SWP						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
C	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.600		
X4	3.500		
Y	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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